

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	67594	non near.volatile near memory	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/16 14:26
L2	78	1 and ((memory near cell near array) with (peripheral near (area region)))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/16 14:40
L3	4	2 and (guard near ring)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/16 14:28
L4	256	1 and (memory near cell near array) and (peripheral near (area region))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/16 14:46
L5	24	4 and (high near voltage near (transistor\$1 circuit\$))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/16 14:41
L6	0	1 and ((dummy near pattern) with (guard near ring))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/16 14:47
L7	0	1 and (dummy near pattern) and (guard near ring)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/16 14:49
L8	6	1 and dummy and (guard near ring)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/16 14:49
L9	28	(dummy near pattern) and (guard near ring)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/16 14:49
S1	2	("6222225").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2004/07/20 11:08

S2	5324	257/239,261,298,315-326.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:08
S3	4472	438/201,211,216,241,257,258,260-266, 591,593.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:10
S4	9114	S2 S3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:10
S5	1987	S4 and (non near volatile near memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:43
S6	186	S5 and ((first near gate near (insulat\$3 oxide dielectric)) with (second near gate near (insulat\$3 oxide dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:18
S7	32	S6 and ((first near thick\$4) with (second near thick\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:14
S8	68	S5 and ((first near gate near (insulat\$3 oxide dielectric)) with (second near gate near (insulat\$3 oxide dielectric)) with thick\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:38
S9	8	S5 and ((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with (second near gate near (insulat\$3 oxide dielectric) near thick\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:43
S10	349594	"257"/\$.ccls. "438"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:43
S11	5004	S10 and (non near volatile near memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/16 14:25

S12	15	S11 and ((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with (second near gate near (insulat\$3 oxide dielectric) near thick\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:49
S13	3	("4471373"   "5194924"   "5237188").PN	USPAT	OR	ON	2004/07/20 11:47
S14	60231	non near volatile near memory	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:49
S15	16	S14 and ((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with (second near gate near (insulat\$3 oxide dielectric) near thick\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:55
S16	44	((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with (greater bigger larger) with (second near gate near (insulat\$3 oxide dielectric) near thick\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:52
S17	179	((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with (second near gate near (insulat\$3 oxide dielectric) near thick\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/07/20 11:55